SPECIFICATION

Product: STW#C2PB-Gx

	Customer				
Drawn by	Drawn by Checked by Approved by				
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24.09.12	24.10.15	24.10.15			

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Mid-Power LED – 3030 G Series STW#C2PB-Gx

(Cool, Neutral, Warm)





















Product Brief

Description

- This White Colored surface-mount LED comes in standard package dimension.
- It has a substrate made up of a molded plastic reflector sitting on top of a lead frame.
- The die is attached within the reflector cavity and the cavity is encapsulated by silicone.
- The package design coupled with careful selection of component materials allow these products to perform with high reliability.

Features and Benefits

- Market Standard 3030 Package Size
- High Color Quality
- Coating Technology to Improve Reliability
- RoHS compliant
- Package Size: 3.0x3.0

Key Applications

- Interior lighting
- · General lighting
- Indoor displays
- Architectural / Decorative lighting



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Product Performance & Characterization Guide

Table 1. Product Selection Guide, I_F = 65mA, T_i = 25°C, RH30%

CRI	ССТ	Performance	Flux & Lm/w(typ) I₅=65mA		
min			G5	G7	
	70001/	Flux	35.8	36.7	
	7000K	lm/w	203.2	209.1	
	CEOOK	Flux	36.4	37.3	
	6500K	lm/w	206.6	212.5	
	F700V	Flux	36.6	37.5	
	5700K	lm/w	207.8	213.7	
	FOOOK	Flux	37.0	37.9	
70	5000K	lm/w	210.0	216.0	
70	4000K	Flux	37.4	38.3	
		lm/w	212.3	218.2	
	3500K	Flux	35.8	36.6	
		lm/w	203.2	208.5	
	3000K	Flux	34.9	35.8	
		lm/w	198.1	204.0	
	2700K	Flux	34.1	34.9	
		lm/w	193.6	198.9	
	6500K	Flux	34.2	35.0	
		lm/w	194.2	199.4	
	57001/	Flux	34.6	35.3	
	5700K	lm/w	196.4	201.1	
	50001/	Flux	35.1	35.8	
	5000K	lm/w	199.3	204.0	
	400016	Flux	34.9	35.6	
00	4000K	lm/w	198.1	202.8	
80	05001/	Flux	34.2	34.9	
	3500K	lm/w	194.2	198.9	
İ	202014	Flux	33.2	33.9	
	3000K	lm/w	188.5	193.2	
	07001/	Flux	32.1	32.8	
	2700K	lm/w	182.2	186.9	
	220014	Flux	29.1	29.7	
	2200K	lm/w	165.2	169.2	

Notes:

- (1) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.
- (2) Seoul Semiconductor maintains a tolerance of ±5% on Flux and power measurements.

The luminous Flux was measured at the peak of the spatial pattern which may not be aligned with the mechanical axis of the LED package.

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Product Performance & Characterization Guide

Table 1. Product Selection Guide, $I_F = 65mA$, $T_j = 25^{\circ}C$, RH30%

CRI	ССТ	Performance	Flux & Lm/w	(typ) I _F =65mA
min			G5	G7
	6500K	Flux	27.6	28.4
	0300K	lm/w	156.7	161.8
	F700K	Flux	27.9	28.7
	5700K	lm/w	158.4	163.5
	5000K	Flux	28.8	29.7
		lm/w	163.5	169.2
90	4000K	Flux	28.3	29.1
90		lm/w	160.7	165.8
	3500K	Flux	27.7	28.5
		lm/w	157.3	162.4
	3000K	Flux	26.7	27.5
	3000K	lm/w	151.6	156.7
	2700K	Flux	25.8	26.6
	2700K	lm/w	146.5	151.6

Notes:

- (1) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.
- (2) Seoul Semiconductor maintains a tolerance of $\pm 5\%$ on Flux and power measurements.

The luminous Flux was measured at the peak of the spatial pattern which may not be aligned with the mechanical axis of the LED package.

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Product Performance & Characterization Guide

Table 2. Characteristics, I_F=65mA, T_i=25°C

Doromotor	Symbol Din		Value			Unit		
Parameter	Symbol	Bin	Min.	Тур.	Max.	Unit		
Forward Voltago	V_F	GxA	-	2.71	-	V		
Forward Voltage	VF	GxB	-	2.78	-	v		
Forward Current	I _F		-	65	-	mA		
			70	72	-			
CRI [3]	R _a	R_{a}	R_a	-	80	82	-	
			90	92	-			
Viewing Angle 2Θ _{1/2}			-	120	-	Deg.		
Thermal resistance (J to S) [4]	ce (J to S) ^[4] Rθ _{J-S}		-	13	-	°C/W		
ESD Sensitivity(HBM) -			Cla	ss 3A JEDE	EC JS-001-20	017		

Table 3. Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Forward Current	I _F	400	mA
Junction Temperature	T_j	125	°C
Operating Temperature	T_{opr}	-40 ~ + 85	°C
Storage Temperature	T _{stg}	-40 ~ + 100	°C

Notes:

- (1) Seoul Semiconductor maintains a tolerance of $\pm 5\%$ on Flux and power measurements.
- (2) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram. Color coordinate: ±0.005, CCT ±5% tolerance.
- (3) Tolerance is ± 2.0 on CRI, ± 0.1 V on VF measurements.
- (4) Thermal resistance is junction to Solder.
- (5) The products are sensitive to static electricity and must be carefully taken when handling products
- (6) It is recommended minimum currrent 5mA in order to avoid unstable brightness, and may vary depending on circuit configuration
- (7) It is recommended to use it in the condition that the reliability is secured within the Max value.
- Calculated performance values are for reference only.
- All measurements were made under the standardized environment of Seoul Semiconductor.

Fig 1. Color Spectrum, T_i=25°C, I_F=65mA

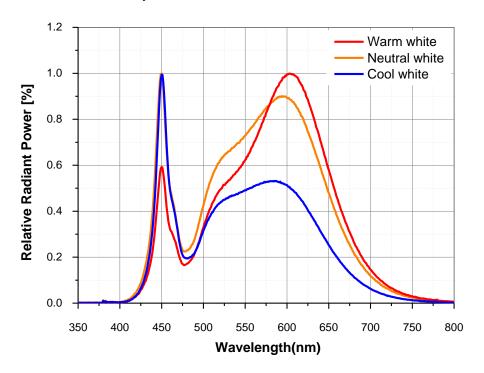


Fig 2. . Radiant pattern 25°C, I_F=65mA

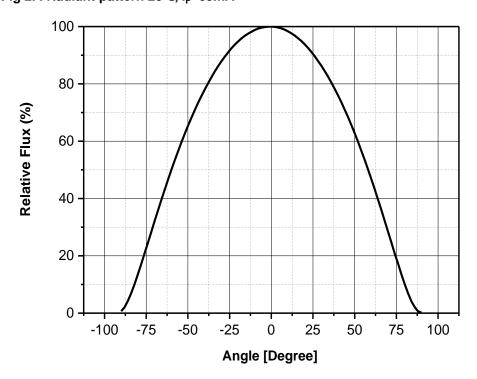




Fig 3. Forward Voltage vs. Forward Current, $T_j = 25^{\circ}C$

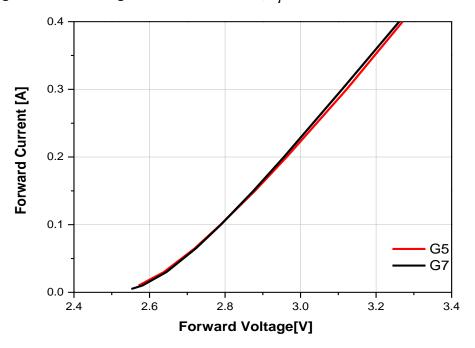
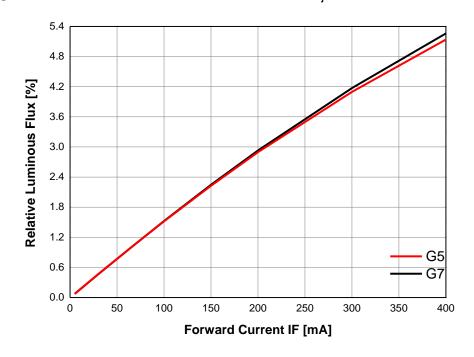


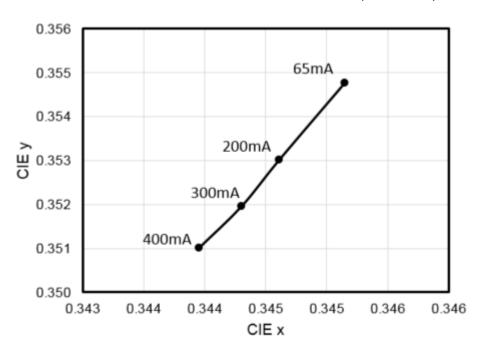
Fig 4. Forward Current vs. Relative Luminous Flux, T_i = 25°C



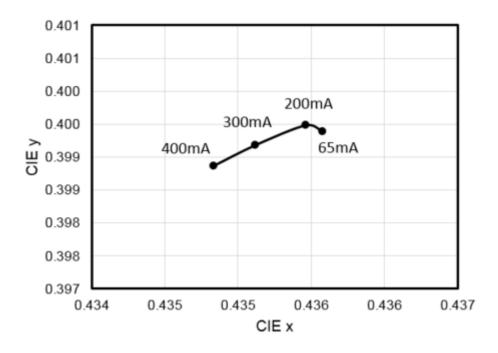
Use of less than 5mA is not recommended

Fig 5. Forward Current vs. CIE X,Y Shift, T_i = 25°C





(2600~4200K)



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Fig 6. Junction Temperature vs. Relative Luminous Flux, I_F=65mA

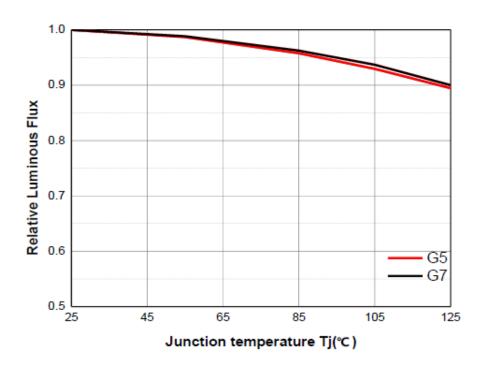


Fig 7. Junction Temperature vs. Relative Forward Voltage, I_F=65mA

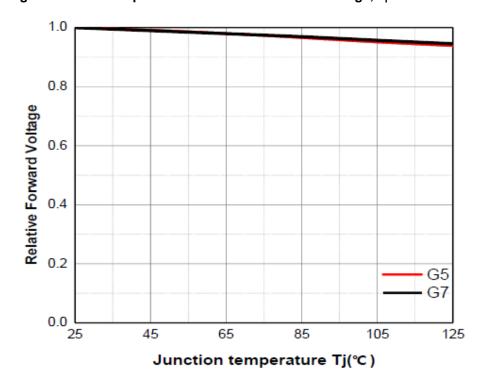
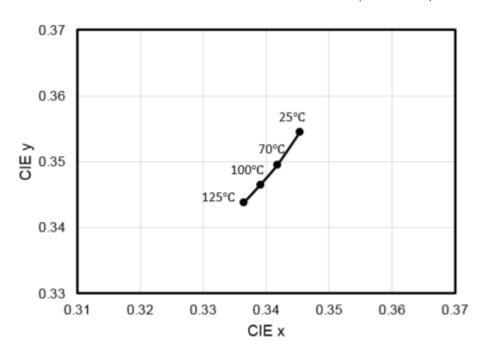
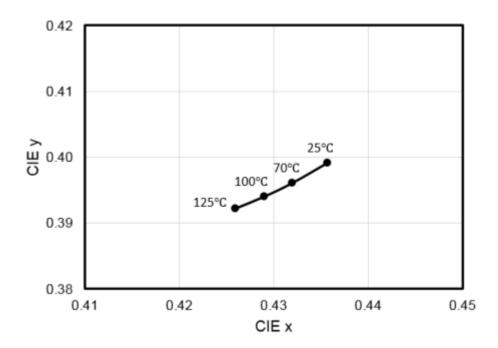


Fig 8. Chromaticity Coordinate vs. Junction Temperature, I_F=65mA

(4200K~7000K)



(2600K~4200K)



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Fig 9. Ambient Temperature vs. Maximum Forward Current, T_{j_max} = 125°C

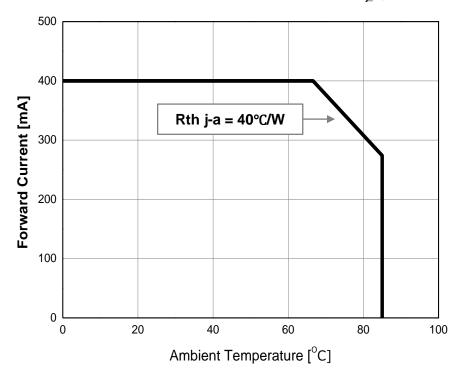




Table 4. Available Flux Rank ,T_i=25°C, I_F=65mA

CDI	Flux Bin	7	G5	70	9 7
CRI	ССТ	min	max	min	max
	7000K	33.5	36.5	34.0	37.0
	6500K	34.0	37.0	34.5	37.5
	5700K	35.0	38.0	35.5	38.5
70	5000K	36.0	39.0	36.5	39.5
/0	4000K	36.0	39.0	36.5	39.5
	3500K	35.0	38.0	35.5	38.5
	3000K	33.5	36.5	34.0	37.0
	2700K	33.0	36.0	33.5	36.5
CRI	Flux Bin	8	G5	80	97
CINI	ССТ	min	max	min	max
	6500K	31.5	34.5	32.5	35.5
	5700K	32.0	35.0	33.0	36.0
	5000K	32.5	35.5	33.5	36.5
80	4000K	32.5	35.5	33.5	36.5
00	3500K	31.5	34.5	32.5	35.5
	3000K	30.5	33.5	32.0	35.0
	2700K	29.5	32.5	30.5	33.5
	2200K	27.0	30.0	28.0	31.0
CRI	Flux Bin	9	G5	90	97
ON	ССТ	min	max	min	max
	6500K	25.0	28.0	25.5	28.5
	5700K	26.0	29.0	26.5	29.5
	5000K	27.0	30.0	27.5	30.5
90	4000K	27.0	30.0	27.5	30.5
	3500K	26.0	29.0	26.5	29.5
	3000K	25.5	28.5	26.0	29.0
	2700K	24.5	27.5	25.0	28.0

^{*} Note:

Flux Bin #Gx: '#' means 7=CRI70,8=CRI80, 9=CRI90

Table 5. Available VF Rank $T_j=25$ °C, $I_F=65$ mA

Item Unit		nit Bin Code	Α		В	
Item	Unit	Bill Code	Min.	Max.	Min.	Max.
Forward Voltage (VF)	V	G5	2.66	2.76	2.76	2.81
	V	G7	2.64	2.74	2.74	2.79

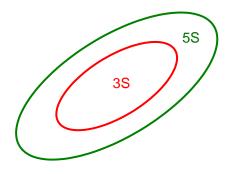
^{*} Note:

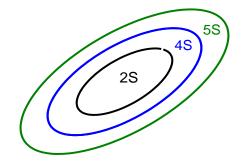
VF rank name will GxA,GxB : 'x' means 5 or 7 series code.

· All measurements were made under the standardized environment of Seoul Semiconductor.



CIE Chromaticity Diagram, T_a=25°C, I_F=65mA





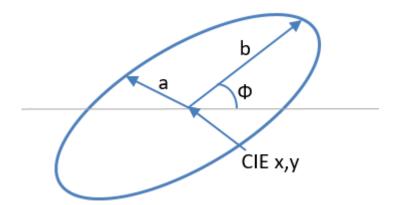
Order	Box Packing Method				
xx3S	3S(3step) Single				
xx4M	3S(3step) & 5S (5step) Mixing				

Order	Box Packing Method				
xx2S	2S(2.3 step) Single				
xx3M	2S(2.3step) & 4S(3.7step) Mixing				
xx4M	2S(2.3step) & 5S(5step) Mixing				

*Notes:

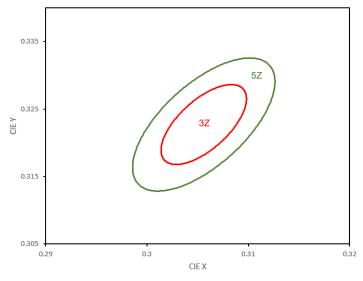
- 1. xx2S Order will ship 2S only
- 2. xx3S Order will ship 3S (=also include 2S)
- 3. xx3M Order will ship 2S & 4S Mixing(=also include 2S and 3S)
- 4. xx4M Order will ship 3S & 5S Or 2S & 5S Mixing(=also include 2S, 3S and 3M)
- 5. Doughnut Bin will not ship alone(=Will ship with mixing bin)
- * 'xx' can be 65=6500K, 56=5600K, 50=5000K, 40=4000K, 30=3000K, 27= 2700K, 22=2200K

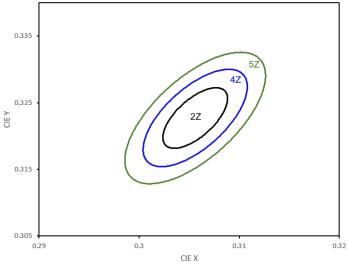
CIE Chromaticity Diagram, T_a=25°C, I_F=65mA



Macadam	ССТ	Cente	er Point	Major Axis	Minor Axis	Rotation Angle
Macadam	(K)	CIE x	CIE y	а	b	Ф
	2700	0.4578	0.4101	0.0081	0.0042	54
	3000	0.4338	0.403	0.0083	0.0040	53
	3500	0.4073	0.3917	0.0093	0.0042	54
3 step	4000	0.3818	0.3797	0.0094	0.0040	54
	5000	0.3447	0.3553	0.0082	0.0035	60
	5700	0.3287	0.3417	0.0076	0.0033	59
	6500	0.3123	0.3282	0.0067	0.0029	59
	2700	0.4578	0.4101	0.0135	0.0070	54
	3000	0.4338	0.403	0.0140	0.0068	53
	3500	0.4073	0.3917	0.0155	0.0069	54
5 step	4000	0.3818	0.3797	0.0156	0.0068	54
	5000	0.3447	0.3553	0.0137	0.0058	60
	5700	0.3287	0.3417	0.0125	0.0053	59
	6500	0.3123	0.3282	0.0112	0.0048	59

CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=7000K

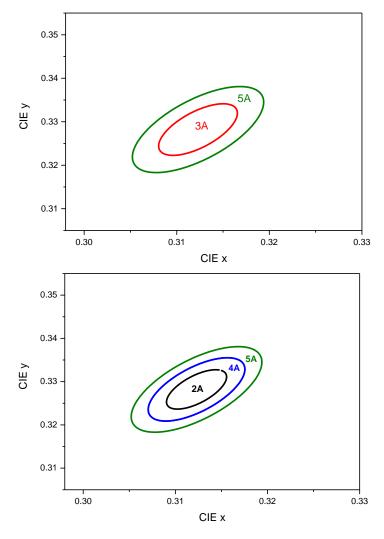




2Z (2	.3Step)	3Z(3.	Ostep)
Center point	0.3056 : 0.3227	Center point	0.3056 : 0.3227
Major Axis a	0.00513	Major Axis a	0.00669
Minor Axis b	0.0022	Minor Axis b	0.00285
Ellipse Rotation Angle	59.12	Ellipse Rotation Angle	59.12

4Z (3.7step)		5Z (5.0Step)		
Center point	0.3056 : 0.3227	Center point	0.3056 : 0.3227	
Major Axis a	0.00825	Major Axis a	0.01115	
Minor Axis b	0.00352	Minor Axis b	0.00475	
Ellipse Rotation Angle	59.12	Ellipse Rotation Angle	59.12	

CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=6500K

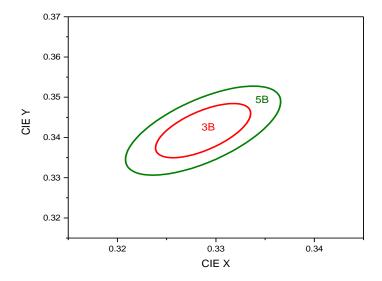


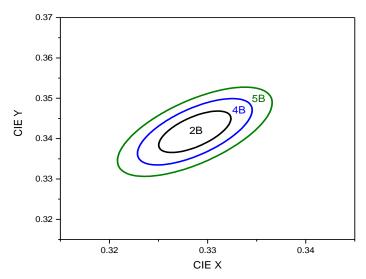
2A (2.3Step)		3A(3.0step)		
Center point	0.3123 :0.3282	Center point	0.3123 : 0.3282	
Major Axis a	0.0051	Major Axis a	0.0067	
Minor Axis b	0.0022	Minor Axis b	0.0029	
Ellipse Rotation Angle	59	Ellipse Rotation Angle	59	

4A (3.7step)		5A (5.0Step)	
Center point	0.3123 : 0.3282	Center point	0.3123 : 0.3282
Major Axis a	0.0083	Major Axis a	0.0112
Minor Axis b	0.0036	Minor Axis b	0.0048
Ellipse	59	Ellipse	59
Rotation Angle	59	Rotation Angle	59



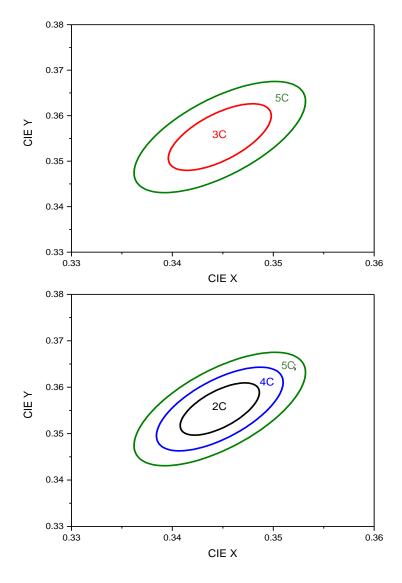
CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=5700K





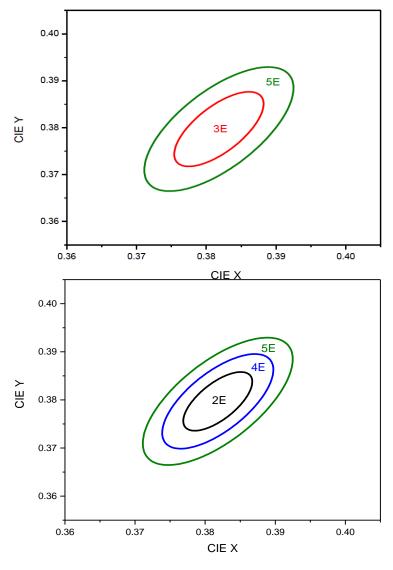
2B (2	2B (2.3Step)		0step)
Center point	0.3287 : 0.3417	Center point	0.3287 : 0.3417
Major Axis a	0.0058	Major Axis a	0.0076
Minor Axis b	0.0025	Minor Axis b	0.0033
Ellipse Rotation Angle	59	Ellipse Rotation Angle	59
		5B (5.0Step)	
4B (3.	7step)	5B (5.	0Step)
4B (3.	7step) 0.3287 : 0.3417	5B (5. Center point	0Step) 0.3287 : 0.3417
· ·	• /	`	
Center point	0.3287 : 0.3417	Center point	0.3287 : 0.3417

CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=5000K



2C (2.3Step)		3C(3.	0step)
Center point	0.3447 : 0.3553	Center point	0.3447 : 0.3553
Major Axis a	0.0063	Major Axis a	0.0082
Minor Axis b	0.0027	Minor Axis b	0.0035
Ellipse Rotation Angle	60	Ellipse Rotation Angle	60
4C (3.	Zoton)	5C (5.0Step)	
4 0 (3.	/step)	ac (a.	ustep)
Center point	0.3447 : 0.3553	Center point	0.3447 : 0.3553
`	• /	•	.,
Center point	0.3447 : 0.3553	Center point	0.3447 : 0.3553

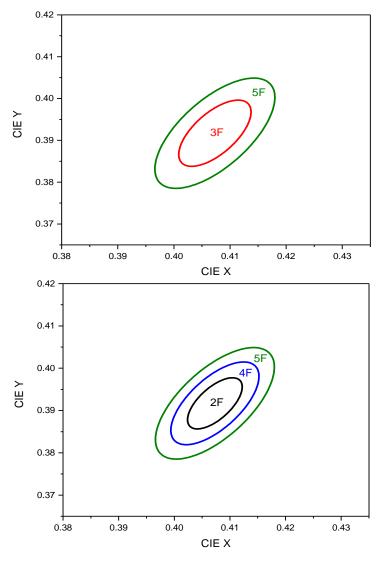
CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=4000K



2E (2	.3Step)	3E(3.0step)	
Center point	0.3818 : 0.3797	Center point	0.3818 : 0.3797
Major Axis a	0.0072	Major Axis a	0.0094
Minor Axis b	0.0031	Minor Axis b	0.0040
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54
		5E (5.0Step)	
4E (3.	7step)	5E (5.	0Step)
4E (3.	7step) 0.3818 : 0.3797	5E (5. Center point	0Step) 0.3818 : 0.3797
·	• /	`	• ′
Center point	0.3818 : 0.3797	Center point	0.3818 : 0.3797



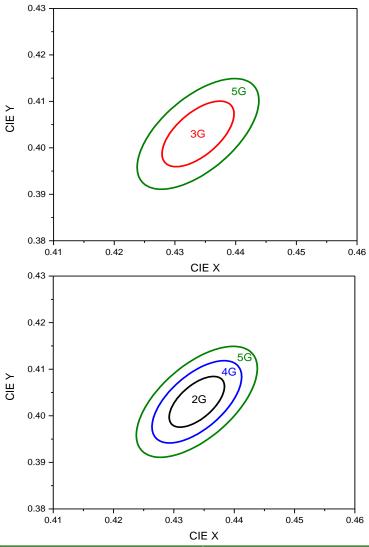
CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=3500K



2F(2	.3Step)	3F(3.0step)		
Center point	0.4073 : 0.3917	Center point	0.4073 : 0.3917	
Major Axis a	0.0071	Major Axis a	0.0093	
Minor Axis b	0.0032	Minor Axis b	0.0042	
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54	
		5F (5.0Step)		
4F (3.	7step)	5F (5.	0Step)	
4F (3.	7step) 0.4073 : 0.3917	5F (5. Center point	0Step) 0.4073 : 0.3917	
Ì	• /	`	• ′	
Center point	0.4073 : 0.3917	Center point	0.4073 : 0.3917	

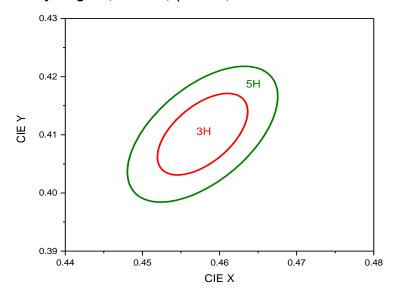


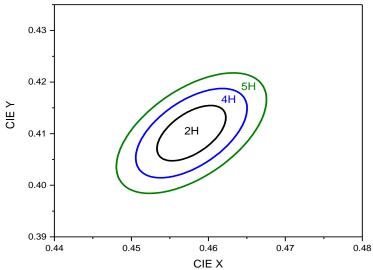
CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=3000K



2G(2	.3Step)	3G (3.0step)		
Center point	0.4338 : 0.4030	Center point	0.4338 : 0.4030	
Major Axis a	0.0064	Major Axis a	0.0083	
Minor Axis b	0.0031	Minor Axis b	0.0040	
Ellipse Rotation Angle	53	Ellipse Rotation Angle	53	
4G 3.	.7step)	5G (5.	0Step)	
4G 3. Center point	7step) 0.4338 : 0.4030	5G (5. Center point	0Step) 0.4338 : 0.4030	
	.,	· ·	.,	
Center point	0.4338 : 0.4030	Center point	0.4338 : 0.4030	

CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=2700K

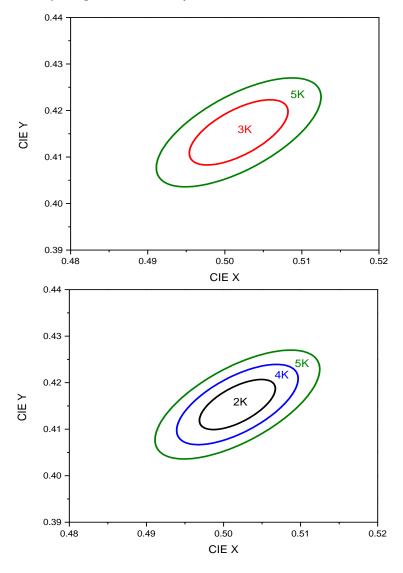




2H(2	.3Step)	3H (3.0step)	
Center point	0.4578 : 0.4101	Center point	0.4578 : 0.4101
Major Axis a	0.0062	Major Axis a	0.0081
Minor Axis b	0.0032	Minor Axis b	0.0042
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54
		5H (5.0Step)	
4H (3.	.7step)	5H (5.	0Step)
4H (3.	7step) 0.4578 : 0.4101	5H (5. Center point	0Step) 0.4578 : 0.4101
· ·	. ,	`	.,
Center point	0.4578 : 0.4101	Center point	0.4578 : 0.4101



CIE Chromaticity Diagram, Ta=25°C, I_F=65mA, CCT=2200K



2K (2.	3Step)	3K (3.0step)	
Center point	0.5018 : 0.4153	Center point	0.5018 : 0.4153
Major Axis a	0.0066	Major Axis a	0.0086
Minor Axis b	0.0031	Minor Axis b	0.0040
Ellipse Rotation Angle	49	Ellipse Rotation Angle	49
4K (3.	7step)	5K (5.	0Step)
4K (3.	7step) 0.5018 : 0.4153	5K (5. Center point	0Step) 0.5018 : 0.4153
· ·	• /	`	.,
Center point	0.5018 : 0.4153	Center point	0.5018 : 0.4153



Mixing order kiting combination

1. Kiting Combination with xx3M

Combination	Reel	FLUX	VF	CIE	Qty
Viting o	Reel 1	8Gx	GxA	2S	12,000pcs
Kiting_a	Reel 2	8Gx	GxA	2S	12,000pcs
Viting h	Reel 1	8Gx	GxA	2S	12,000pcs
Kiting_b	Reel 2	8Gx	GxA	4S	12,000pcs
Viting o	Reel 1	8Gx	GxA	2S	12,000pcs
Kiting_c	Reel 2	8Gx	GxB	2S	12,000pcs
Kiting d	Reel 1	8Gx	GxA	2S	12,000pcs
Kiting_d	Reel 2	8Gx	GxB	4S	12,000pcs

^{*} Gx can be G5~G7

2. Kiting Combination with xx4M

Combination	Reel	FLUX	VF	CIE	Qty
Viting o	Reel 1	8Gx	GxA	2S	12,000pcs
Kiting_a	Reel 2	8Gx	GxA	2S	12,000pcs
Viting h	Reel 1	8Gx	GxA	2S	12,000pcs
Kiting_b	Reel 2	8Gx	GxA	5S	12,000pcs
Viting o	Reel 1	8Gx	GxA	2S	12,000pcs
Kiting_c	Reel 2	8Gx	GxB	2S	12,000pcs
Viting d	Reel 1	8Gx	GxA	2S	12,000pcs
Kiting_d	Reel 2	8Gx	GxB	5S	12,000pcs
Viting	Reel 1	8Gx	GxA	3S	12,000pcs
Kiting_e	Reel 2	8Gx	GxA	3S	12,000pcs
Viting f	Reel 1	8Gx	GxA	3S	12,000pcs
Kiting_f	Reel 2	8Gx	GxA	5S	12,000pcs
Viting a	Reel 1	8Gx	GxA	3S	12,000pcs
Kiting_g	Reel 2	8Gx	GxB	3S	12,000pcs
Viting h	Reel 1	8Gx	GxA	3S	12,000pcs
Kiting_h	Reel 2	8Gx	GxB	5S	12,000pcs

^{*} Gx can be G5 or G7.



Order Code Nomenclature

Table 6. Nomenclature example



Part Number Code	Value	References	Description
X ₁	S	Seoul Semiconductor	Company
X ₂	Т	Top lighting	Top View LED series
X ₃	W	White	
X ₄	#	CRI	7: CRI70/ 8: CRI 80 / 9: CRI90
X ₅	С	3030	Package series
X ₆ X ₇	2P	Characteristic code	S: Series / P: Parallel
X ₈	В		Version
X ₉	-		
X ₁₀ X ₁₁	Gx	internal code	G5/G7
X ₁₂ ~X ₂₀	00C1ZP000	internal code	
X ₂₁ X ₂₂ X ₂₃	abb	Flux Bin	a: 7=CRI70 8=CRI80, 9=CRI90 bb: G5/G7/G9
X ₂₄ X ₂₅	CC	Color Temp.	65=6500K, 56=5600K, 50=5000K, 40=4000K, 30=3000K, 27= 2700K, 22=2200K
X ₂₆ X ₂₇	dd	step	2S:2step single /3S: 3step single / 3M: 3step Mixing / 4M: 4step Mixing
X ₂₈ X ₂₉ X ₃₀	eee	VF Bin	000: All bin

Table 7. Product Selection Table

Reference P/N	Order code	Flux bin	ССТ	Step	VF bin
	7Gx702SGxA	7Gx:7G5,7G7	70:7000K		GxA
	7Gx652SGxA	7Gx:7G5,7G7	65:6500K		GxA
	7Gx572SGxA	7Gx:7G5,7G7	57:5700K	2S: 2step 3S: 3step	GxA
STW7C2PB-	7Gx502SGxA	7Gx:7G5,7G7	50:5000K		GxA
Gx00C1ZP000	7Gx402SGxA	7Gx:7G5,7G7	40:4000K		GxA
	7Gx352SGxA	7Gx:7G5,7G7	35:3500K		GxA
	7Gx302SGxA	7Gx:7G5,7G7	30:3000K	•	GxA
	7Gx272SGxA	7Gx:7G5,7G7	27:2700K		GxA
	8Gx652SGxA	8Gx:8G5,8G7	65:6500K	2S: 2step 3S: 3step	GxA
	8Gx572SGxA	8Gx:8G5,8G7	57:5700K		GxA
	8Gx502SGxA	8Gx:8G5,8G7	50:5000K		GxA
STW8C2PB-	8Gx402SGxA	8Gx:8G5,8G7	40:4000K		GxA
Gx00C1ZP000	8Gx352SGxA	8Gx:8G5,8G7	35:3500K		GxA
	8Gx302SGxA	8Gx:8G5,8G7	30:3000K		GxA
	8Gx272SGxA	8Gx:8G5,8G7	27:2700K		GxA
	8Gx222SGxA	8Gx:8G5,8G7	22:2200K		GxA
	9Gx652SGxA	9Gx:9G5,9G7	65:6500K	2S: 2step 3S: 3step	GxA
	9Gx572SGxA	9Gx:9G5,9G7	57:5700K		GxA
	9Gx502SGxA	9Gx:9G5,9G7	50:5000K		GxA
STW9C2PB- Gx00C1ZP000	9Gx402SGxA	9Gx:9G5,9G7	40:4000K		GxA
5,000 12, 000	9Gx352SGxA	9Gx:9G5,9G7	35:3500K	00. oo.op	GxA
	9Gx302SGxA	9Gx:9G5,9G7	30:3000K		GxA
	9Gx272SGxA	9Gx:9G5,9G7	27:2700K		GxA



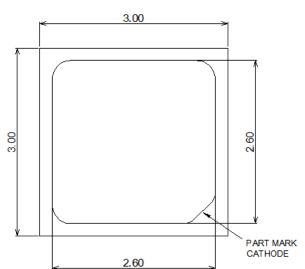
Order Code Nomenclature

Table 7. Product Selection Table

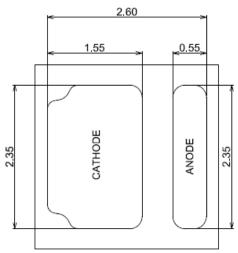
Reference P/N	Order code	Flux bin	ССТ	Step	VF bin
	7Gx703M000	7Gx:7G5,7G7	70:7000K		ALL
	7Gx653M000	7Gx:7G5,7G7	65:6500K		ALL
	7Gx573M000	7Gx:7G5,7G7	57:5700K		ALL
STW7C2PB-	7Gx503M000	7Gx:7G5,7G7	50:5000K		ALL
Gx00C1ZP000	7Gx403M000	7Gx:7G5,7G7	40:4000K		ALL
	7Gx353M000	7Gx:7G5,7G7	35:3500K		ALL
	7Gx303M000	7Gx:7G5,7G7	30:3000K		ALL
	7Gx273M000	7Gx:7G5,7G7	27:2700K		ALL
	8Gx653M000	8Gx:8G5,8G7	65:6500K	3M: 3step Mixing 4M: 4step Mixing	ALL
	8Gx573M000	8Gx:8G5,8G7	57:5700K		ALL
	8Gx503M000	8Gx:8G5,8G7	50:5000K		ALL
STW8C2PB-	8Gx403M000	8Gx:8G5,8G7	40:4000K		ALL
Gx00C1ZP000	8Gx353M000	8Gx:8G5,8G7	35:3500K		ALL
	8Gx303M000	8Gx:8G5,8G7	30:3000K		ALL
	8Gx273M000	8Gx:8G5,8G7	27:2700K		ALL
	8Gx223M000	8Gx:8G5,8G7	22:2200K		ALL
	9Gx653M000	9Gx:9G5,9G7	65:6500K	3M: 3step Mixing 4M: 4step Mixing	ALL
	9Gx573M000	9Gx:9G5,9G7	57:5700K		ALL
	9Gx503M000	9Gx:9G5,9G7	50:5000K		ALL
STW9C2PB- Gx00C1ZP000	9Gx403M000	9Gx:9G5,9G7	40:4000K		ALL
3,000121 000	9Gx353M000	9Gx:9G5,9G7	35:3500K		ALL
	9Gx303M000	9Gx:9G5,9G7	30:3000K		ALL
	9Gx273M000	9Gx:9G5,9G7	27:2700K		ALL

Mechanical Dimensions

Top View



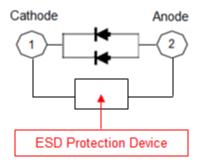
Bottom View



Side View







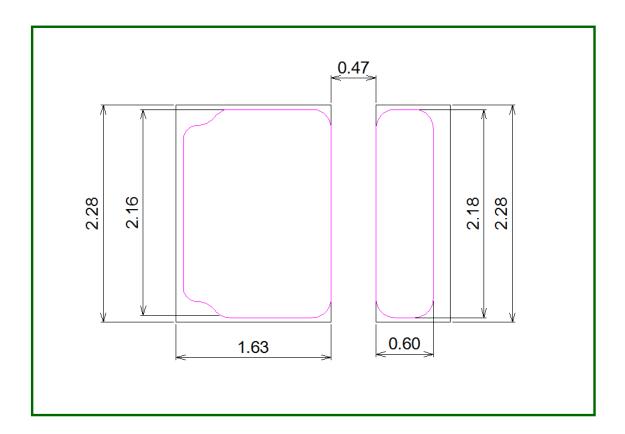
Notes:

(1) All dimensions are in millimeters.

(2) Scale: none

(3) Undefined tolerance is $\pm 0.2 \text{mm}$

Recommended Solder Pad



Note:

- (1) All dimensions are in millimeters.
- (2) Scale: none
- (3) This drawing without tolerances are for reference only
- (4) Undefined tolerance is ± 0.1 mm
- (5) The appearance and specifications of the product may be changed for improvement without notice.

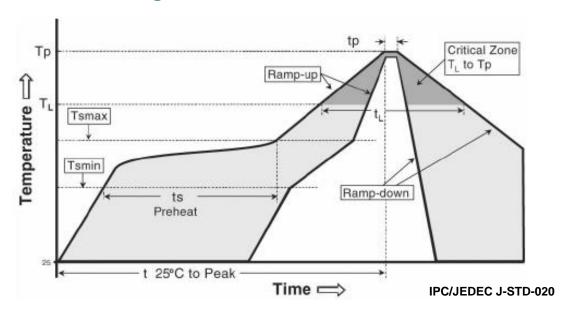
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Reliability Test Item & Condition

Test Item	Test conditions	Time/cycle	Q'ty
High Temperature Operating Life	Ta = 85°C	1000	20
Low Temperature Operating Life	T _{amb} -40 °C. or -20 °C with On/Off(5min/5min)	1000	20
Temperature Shock	Ta = -40 °C ↔ 120 °C, Dwell time : 30 min (on PCB)	1000	40
High Temperature High Humidity	Ta=85℃, RH=85%	1000	10
H2S corrosion	40℃ / 80%, H2S 15ppm	504	10
ESD	HBM, 2KV, 1.5kΩ, 100pF, Alternately positive or negative	-	20

Reflow Soldering Characteristics



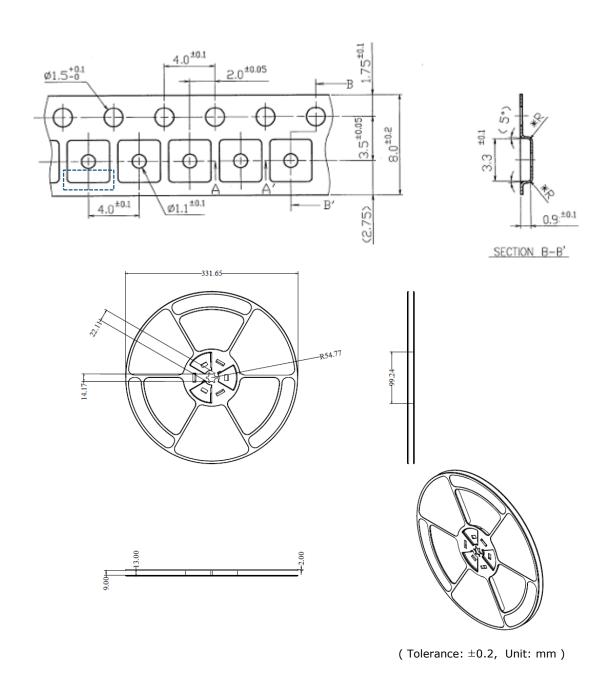
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _{smax} to T _p)	3° C/second max.	3° C/second max.
Preheat - Temperature Min (T _{smin}) - Temperature Max (T _{smax}) - Time (T _{smin} to T _{smax}) (t _s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-180 seconds
Time maintained above: - Temperature (T _L) - Time (t _L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak Temperature (T _p)	215°C	260°C
Time within 5°C of actual Peak Temperature (t _p)2	10-30 seconds	20-40 seconds
Ramp-down Rate	6 °C/second max.	6 °C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Caution

- (1) Reflow soldering is recommended not to be done more than two times. In the case of more than 24 hours passed soldering after first, LEDs will be damaged.
- (2) Repairs should not be done after the LEDs have been soldered. When repair is unavoidable, suitable tools must be used.
- (3) Die slug is to be soldered.
- (4) When soldering, do not put stress on the LEDs during heating.
- (5) After soldering, do not warp the circuit board.

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Emitter Tape & Reel Packaging



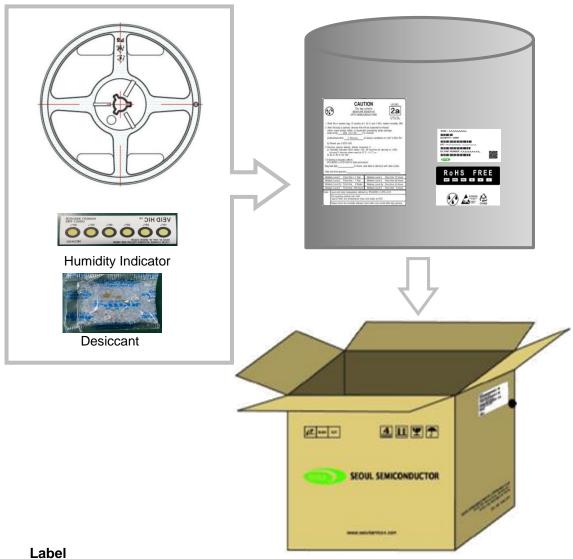
Notes:

- (1) Quantity: Max 12,000pcs/Reel
- (2) Cumulative Tolerance : Cumulative Tolerance/10 pitches to be ± 0.2 mm
- (3) Adhesion Strength of Cover Tape

 Adhesion strength to be 0.1-0.7N when the cover tape is turned off from the carrier tape at the angle of 10° to the carrier tape.
- (4) Package : P/N, Manufacturing data Code No. and Quantity to be indicated on a damp proof Package.

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Emitter Tape & Reel Packaging



 $RANK: Z_1Z_1Z_2Z_2Z_3Z_3Z_3$ **QUANTITY: 12000** | 1204| 110 | 1204| | 1404| | 1404| | 1604| 1604| 1604| 1604| 1604| **LOT**: $Y_1Y_2Y_3Y_4Y_5Y_6Y_7Y_8Y_9Y_{10} - Y_{11}Y_{12}Y_{13}Y_{14}Y_{15}Y_{16}Y_{17}$ **SSC PART NUMBER**: $x_1x_2x_3x_4x_5x_6x_7x_8-x_9x_{10}$ | 1818| 182 | 1868| | | 1868| 1888| 1888| 1888| 1888| 1888|

Notes:

(1) Rank : Flux: $Z_1Z_1Z_1$, CIE: Z_2Z_2 , VF: $Z_3Z_3Z_3$

(2) Quantity: Max 12000pcs/Reel

(3) Lot no.: $Y_1Y_2Y_3Y_4Y_5Y_6Y_7Y_8Y_9Y_{10}$ – SSC code $-Z_1Z_1Z_1Z_2Z_2Z_2Z_3Z_3Z_3$ (4) SSC part Number : $X_1X_2X_3X_4X_5X_6X_7X_8-X_9X_{10}$

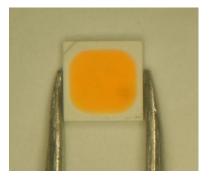


Handling of Silicone Resin for LEDs

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.



(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.



- (3) When populating boards in SMT production, there are basically no restrictions regarding the form of the pick and place nozzle, except that mechanical pressure on the surface of the resin must be prevented. This is assured by choosing a pick and place nozzle which is larger than the LED's reflector area.
 - (4) Silicone differs from materials conventionally used for the manufacturing of LEDs. These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust.

As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of components.

- (5) SSC suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin.

 Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.
- (6) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this. product with acid or sulfur material in sealed space.

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Precaution for Use

(1) Storage

To avoid the moisture penetration, we recommend store in a dry box with a desiccant.

The maximum storage temperature range is 40°C and a maximum humidity of RH90%.

(2) Use Precaution after Opening the Packaging

Use SMT techniques properly when the LED is to be soldered dipped as separation of the lens may affect the light output efficiency.

Pay attention to the following:

- a. Recommend conditions after opening the package
 - Sealing
 - Temperature : 30°C Humidity : less than RH60%
- b. If the package has been opened more than 4 week(MSL_2a) or the color of the desiccant changes, components should be dried for 10-24hr at 65±5°C
- (3) Do not apply mechanical force or excess vibration during the cooling process to normal temperature after soldering.
- (4) Do not rapidly cool device after soldering.
- (5) Components should not be mounted on warped (non coplanar) portion of PCB.
- (6) Radioactive exposure is not considered for the products listed here in.
- (7) Gallium arsenide is used in some of the products listed in this publication. These products are dangerous if they are burned or shredded in the process of disposal. It is also dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.
- (8) This device should not be used in any type of fluid such as water, oil, organic solvent and etc. When washing is required, IPA (Isopropyl Alcohol) should be used.
- (9) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.
- (10) Don't recommend to use it for cold storage lighting.

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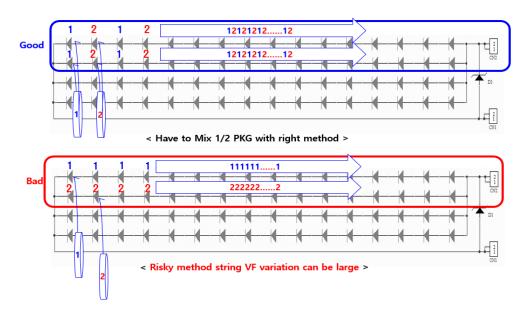
Precaution for Use

- (11) The appearance and specifications of the product may be modified for improvement without notice.
- (12) Long time exposure of sunlight or occasional UV exposure will cause lens discoloration.
- (13) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.
- (14) Attaching LEDs, do not use adhesives that outgas organic vapor.
- (15) The driving circuit must be designed to allow forward voltage only when it is ON or OFF.

 If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.
- (16) Similar to most Solid state devices;
 LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS).
 Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.
- (17) Voltage Variation Mixing

If Module circuit series and parallel many PKG, voltage variation problem coming out seriously. To avoid this issue we recommend mixing Vf bin at the SMD Module Program level. Even though using Single bin only.

For example, when configuring a module with two reels (reel1 and Reel2), SMT should be as follows Good below.



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Precaution for Use

a. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event.

One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:

- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

Environmental controls:

- Humidity control (ESD gets worse in a dry environment)

b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package
 (If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)
- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package (shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.
- c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:
 - A surge protection circuit
 - An appropriately rated over voltage protection device
 - A current limiting device

Company Information

Published by

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Company Information

Seoul Semiconductor (www.SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotive, general illumination/lighting, Home appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology" a proprietary family of high-voltage LEDs.

The company's broad product portfolio includes a wide array of package and device choices such as Acrich and Acirch2, high-brightness LEDs, mid-power LEDs, side-view LEDs, and through-hole type LEDs as well as custom modules, displays, and sensors.

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